

NCE P-Channel Enhancement Mode Power MOSFET

Description

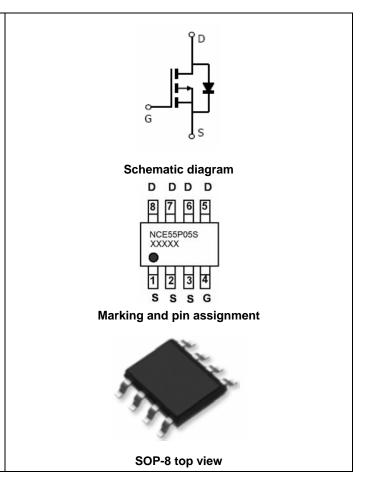
The NCE55P05S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =-55V, I_{D} =-5A $R_{DS(ON)}$ <80m Ω @ V_{GS} =-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC Converter



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE55P05S	NCE55P05S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-55	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-5	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-3.0	Α
Pulsed Drain Current	I _{DM}	-25	А
Maximum Power Dissipation	P _D	3	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance ,Junction-to-Ambient ^(Note 2)	R _{θJA}	42	°C/W
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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -55		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-55V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.5	-2.6	-3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5A	-	64	80	mΩ
Forward Transconductance	g FS	V _{DS} =-15V,I _D =-5A	16	-	-	S
Dynamic Characteristics (Note4)	•		•	•		
Input Capacitance	C _{lss}	V 00VVV 0V	-	1450	-	PF
Output Capacitance	Coss	V_{DS} =-20V, V_{GS} =0V, F=1.0MHz	-	145	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	110	-	PF
Switching Characteristics (Note 4)				•		
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, , R_L =30 Ω	-	9	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{GEN} =6 Ω	-	65	-	nS
Turn-Off Fall Time	t _f		-	30	-	nS
Total Gate Charge	Qg	\/ - 20\/ - 54	-	26	-	nC
Gate-Source Charge	Q_{gs}	V_{DS} =-30V, I_{D} =-5A, V_{GS} =-10V	-	4.5	-	nC
Gate-Drain Charge	Q_{gd}	v _{GS} =-10v	-	7	-	nC
Drain-Source Diode Characteristics			-			
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =-5 A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-5	Α

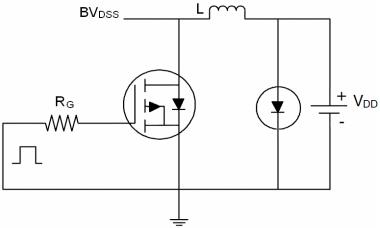
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

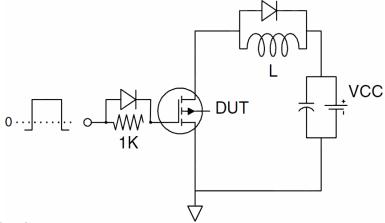


Test Circuit

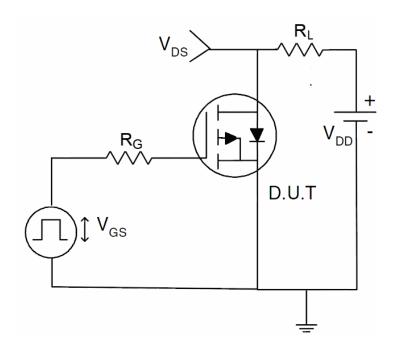
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

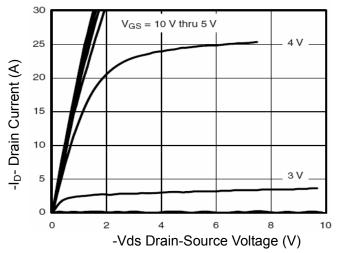


Figure 1 Output Characteristics

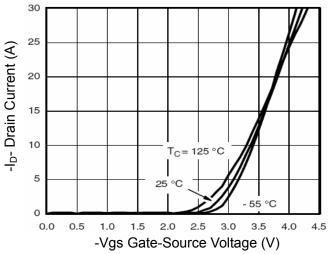


Figure 2 Transfer Characteristics

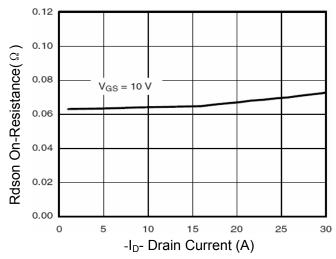


Figure 3 Rdson- Drain Current

(Curves)

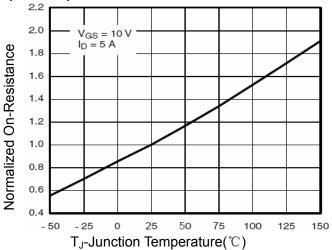


Figure 4 Rdson-Junction Temperature

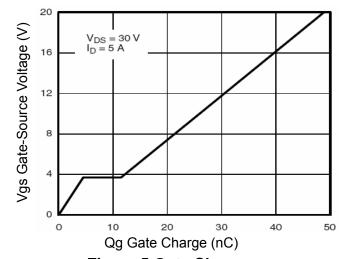


Figure 5 Gate Charge

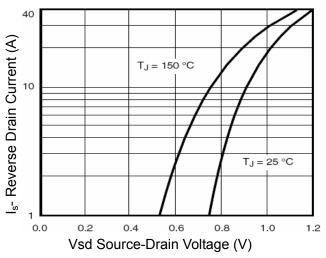


Figure 6 Source- Drain Diode Forward



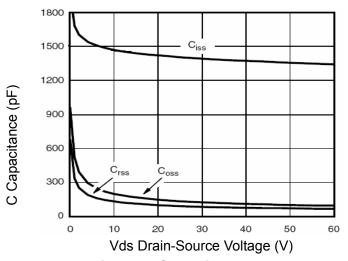
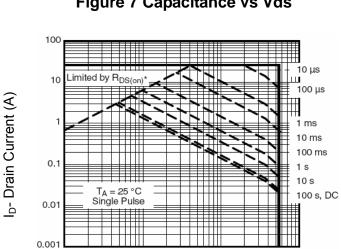


Figure 7 Capacitance vs Vds



Vds Drain-Source Voltage (V) **Figure 8 Safe Operation Area**

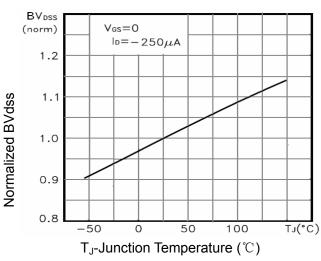


Figure 9 BV_{DSS} vs Junction Temperature

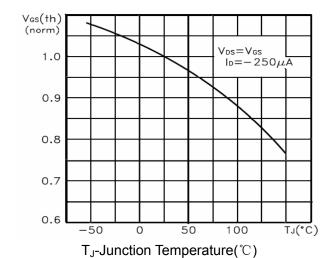


Figure 10 V_{GS(th)} vs Junction Temperature

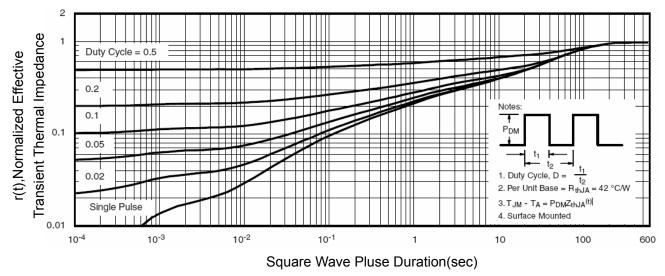
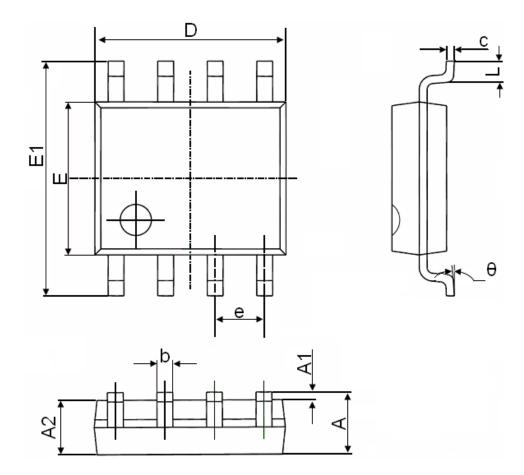


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	1.270(BSC)		(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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